# Fabrication of Perovskite PV devices using Ossila I201 Ink

# **Process summary**

## 1. Substrate clean (in air)

Sonicate ITO substrates for 5 minutes in hot (~70°C) 1% Hellmanex (Ossila C141) Dump-rinse substrates twice in boiling, deionised (DI) water Sonicate for 5 mins in IPA Dump-rinse twice in boiling DI water Dry the substrates with a nitrogen gun Bake the substrates on a hotplate at ~120°C

# 2. PEDOT:PSS anode preparation (in air)

Filter AI 4083 PEDOT:PSS (Ossila M121) using a  $0.45\mu m$  PVDF filter (Ossila C105) Dispense 35  $\mu$ l of the filtered PEDOT:PSS solution onto the heated ITO substrate spinning at 6000 rpm for 30s

Place substrate onto a hotplate at ~120°C

After all ITO substrates have been coated, transfer all to a nitrogen-filled glovebox and place onto a hotplate at  $120^{\circ}$ C for ~20-30 mins

Remove the substrates from the hotplate and allow to cool at room temperature

### 3. Perovskite deposition (in nitrogen glovebox)

Heat I201 perovskite ink for 2 hours at ~70°C and then cool to room temperature

Place the ITO coated substrate (at room temperature) onto the spin-coater and spin the substrate at 4000 rpm (for 30s)

Dynamically dispense  $30\mu l$  of I201 ink

Place substrate back onto the hotplate (in the glovebox) at ~80°C.

Once all substrates have been coated, anneal for ~90 mins

After 90 mins, use a cleaning swab dipped in DMF solvent to wipe the cathode stripe clean After cleaning, anneal for an addition 20-30 mins at 80°C to remove any residual DMF solvent. After

this time, remove substrates from the hotplate and cool to room temperature.

### 4. PC70BM deposition (in nitrogen glovebox)

Prepare a solution of  $PC_{70}BM$  (Ossila M113) at 50 mg/ml in chlorobenzene and stir for 3 to 5 hours Place perovskite coated substrate onto the spin-coater and spin at 1000 rpm.

Dispense 20 µl of PC70BM solution onto the substrate (while spinning) and spin for a total time of 30s

# 5. Cathode deposition and encapsulation

Thermally evaporate a calcium/aluminium cathode (5 and 100 nm respectively) through a shadow-mask (Ossila E341)

Encapsulate devices using a glass coverslip (Ossila C181) and encapsulation epoxy (Ossila E131)

Expose to UV radiation (350 nm) for 30 mins to cure the epoxy